

BAX12/BAX12A

CONTROLLED AVALANCHE DIODES

Features

- Switching speed: max. 50 ns
- Continuous reverse voltage: max. 90V
- Repetitive peak reverse voltage: max. 90V
- Repetitive peak forward current: max.800 mA
- Repetitive peak reverse current: max.600mA

Mechanical Data

Case: DO-35 Glass Case

 Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed

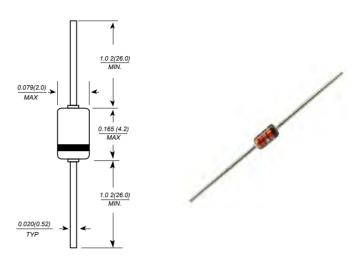
Polarity : Color band denotes cathode end

Mounting position : Any

Weight: 0.13 gram (approximately)



DO-35(GLASS)



Dimensions in millimeters

Maximum Ratings @ TA = 25°C unless otherwise specified

Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V_{RRM}	90	V
Continuous Reverse Voltage		V _R	90	V
Continuous Forward Current		I _F	400	mA
Repetitive Peak Forward Current		I _{FRM}	800	А
Non-repetitive Peak Forward Current	t = 1 μs		55	
Square wave: Tj = 25 °C prior to surge	t = 100 μs	I _{FSM}	15	Α
	t = 10 ms		9	
Total Power Dissipation , Ta = 25 °C		P _{tot}	450	mW
Repetitive Peak Reverse Current		I _{RRM}	600	mA
Junction Temperature		T _J	200	°C
Storage Temperature Range		T _S	-65 to + 200	°C

 $\textbf{Note:} (1) \ \mathsf{Device} \ \mathsf{mounted} \ \mathsf{on} \ \mathsf{an} \ \mathsf{FR4} \ \mathsf{printed} \ \mathsf{circuit}\text{-}\mathsf{board}; \ \mathsf{lead} \ \mathsf{length} \ \mathsf{10} \ \mathsf{mm}.$

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Test Condition	Min.	Max.	Unit
Reverse Avalanche	BAX12	V	I _R = 1mA	120	170	V
Breakdown Voltage	BAX12A	$V_{(BR)R}$	$I_R = 0.1 \text{mA}$	120	170	V
Deverse Current		1	V _R = 90 V	-	100	nA
Reverse Current		I _R	V _R = 90 V, Tj = 150 °C	-	100	μΑ
Forward Voltage		V _F	I _F = 400 mA	-	1.25	V
Diode Capacitance		Cd	f = 1MHz ; V _R = 0	-	35	pF
			I _F = 30mA , I _R = 30mA			
Reverse Recovery Time		Trr	R_L = 100 Ω measured at	-	50	ns
			I _R = 3 mA			



RATING AND CHARACTERISTIC CURVES (BAX12, BAX12A)

Fig.1 - Maximum permissible continuous forward current as a function of ambient temperature.

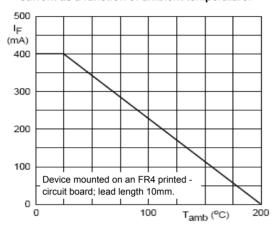


Fig.3 - Reverse current as a function of junction temperature.

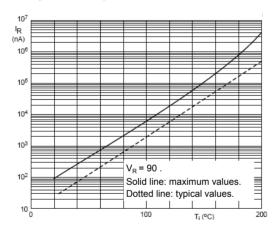


Fig.2 - Forward current as a function of forward voltage.

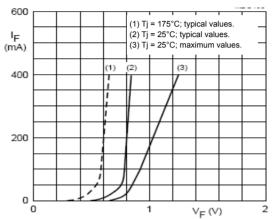


Fig.4 - Diode capacitance as a function of reverse voltage; typical values.

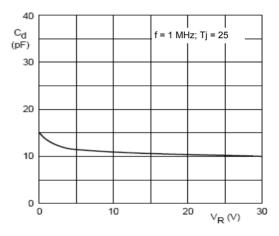


Fig.5 - Maximum permissible non-repetitive peak forward current as a function of pulse duration.

